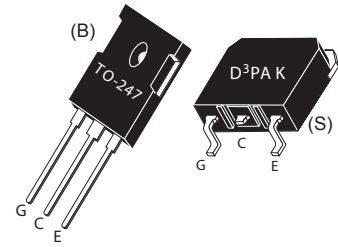


Ultra Fast NPT - IGBT®

The Ultra Fast NPT - IGBT® is a new generation of high voltage power IGBTs. Using Non-Punch-Through Technology, the Ultra Fast NPT-IGBT® offers superior ruggedness and ultrafast switching speed.

Features

- Low Saturation Voltage
- Low Tail Current
- RoHS Compliant 
- Short Circuit Withstand Rated
- High Frequency Switching to 50KHz
- Ultra Low Leakage Current



Unless stated otherwise, Microsemi discrete IGBTs contain a single IGBT die. This device is recommended for applications such as induction heating (IH), motor control, general purpose inverters and uninterruptible power supplies (UPS).

MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ C$ unless otherwise specified.

Symbol	Parameter	Ratings	Unit
V_{CES}	Collector Emitter Voltage	1200	V
V_{GE}	Gate-Emitter Voltage	± 30	
I_{C1}	Continuous Collector Current @ $T_C = 25^\circ C$	88	A
I_{C2}	Continuous Collector Current @ $T_C = 100^\circ C$	40	
I_{CM}	Pulsed Collector Current ^①	160	
SCWT	Short Circuit Withstand Time: $V_{CE} = 600V$, $V_{GE} = 15V$, $T_C = 125^\circ C$	10	μs
P_D	Total Power Dissipation @ $T_C = 25^\circ C$	500	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	$^\circ C$
T_L	Max. Lead Temp. for Soldering: 0.063" from Case for 10 Sec.	300	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Min	Typ	Max	Unit
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage ($V_{GE} = 0V$, $I_C = 1.0mA$)	1200			Volts
$V_{GE(TH)}$	Gate Threshold Voltage ($V_{CE} = V_{GE}$, $I_C = 2.0mA$, $T_J = 25^\circ C$)	3.5	5.0	6.5	
$V_{CE(ON)}$	Collector-Emitter On Voltage ($V_{GE} = 15V$, $I_C = 40A$, $T_J = 25^\circ C$)		2.5	3.2	
	Collector-Emitter On Voltage ($V_{GE} = 15V$, $I_C = 40A$, $T_J = 125^\circ C$)		3.5		
	Collector-Emitter On Voltage ($V_{GE} = 15V$, $I_C = 88A$, $T_J = 25^\circ C$)		3.2		
I_{CES}	Collector Cut-off Current ($V_{CE} = 1200V$, $V_{GE} = 0V$, $T_J = 25^\circ C$) ^②		10	1000	μA
	Collector Cut-off Current ($V_{CE} = 1200V$, $V_{GE} = 0V$, $T_J = 125^\circ C$) ^②		100		
I_{GES}	Gate-Emitter Leakage Current ($V_{GE} = \pm 20V$)			± 250	nA



CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

DYNAMIC CHARACTERISTICS

APT40GR120B_S

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	Capacitance $V_{GE} = 0V, V_{CE} = 25V$ $f = 1MHz$		3980		pF
C_{oes}	Output Capacitance			320		
C_{res}	Reverse Transfer Capacitance			80		
V_{GEP}	Gate to Emitter Plateau Voltage	Gate Charge $V_{GE} = 15V$ $V_{CE} = 600V$ $I_C = 40A$		7		V
$Q_g^{(3)}$	Total Gate Charge			210		nC
Q_{ge}	Gate-Emitter Charge			25		
Q_{gc}	Gate- Collector Charge			90		
$t_{d(on)}$	Turn-On Delay Time	Inductive Switching (25°C) $V_{CC} = 600V$ $V_{GE} = 15V$ $I_C = 40A$ $R_G = 4.3 \Omega^{(4)}$ $T_J = +25^\circ C$		22		ns
t_r	Current Rise Time			25		
$t_{d(off)}$	Turn-Off Delay Time			163		
t_f	Current Fall Time			40		
$E_{on2}^{(5)}$	Turn-On Switching Energy			1375	3000	μJ
$E_{off}^{(6)}$	Turn-Off Switching Energy			906	1650	
$t_{d(on)}$	Turn-On Delay Time	Inductive Switching (125°C) $V_{CC} = 600V$ $V_{GE} = 15V$ $I_C = 40A$ $R_G = 4.3 \Omega^{(4)}$ $T_J = +125^\circ C$		22		ns
t_r	Current Rise Time			25		
$t_{d(off)}$	Turn-Off Delay Time			185		
t_f	Current Fall Time			47		
$E_{on2}^{(5)}$	Turn-On Switching Energy			1916	3500	μJ
$E_{off}^{(6)}$	Turn-Off Switching Energy			1186	2500	

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic	Min	Typ	Max	Unit
$R_{\theta JC}$	Junction to Case Thermal Resistance			.25	°C/W
$R_{\theta JA}$	Junction to Ambient Thermal Resistance			40	
W_T	Package Weight		.22		oz
			6.2		g
Torque	Mounting Torque (TO-247 Package), 4-40 or M3 screw			10	in-lbf
				6.2	N·m

1 Repetitive Rating: Pulse width and case temperature limited by maximum junction temperature.

2 Pulse test: Pulse Width < 380μs, duty cycle < 2%.

3 See Mil-Std-750 Method 3471.

4 R_G is external gate resistance, not including internal gate resistance or gate driver impedance. (MIC4452)

5 E_{on2} is the clamped inductive turn on energy that includes a commutating diode reverse recovery current in the IGBT turn on energy loss. A combi device is used for the clamping diode.

6 E_{off} is the clamped inductive turn-off energy measured in accordance with JEDEC standard JESD24-1.

Microsemi reserves the right to change, without notice, the specifications and information contained herein.

TYPICAL PERFORMANCE CURVES

APT40GR120B_S

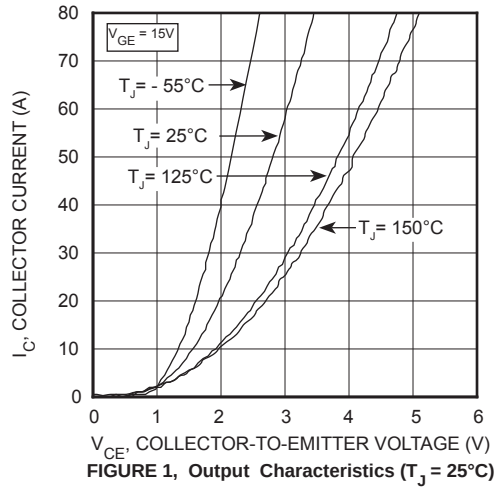


FIGURE 1, Output Characteristics ($T_J = 25^\circ\text{C}$)

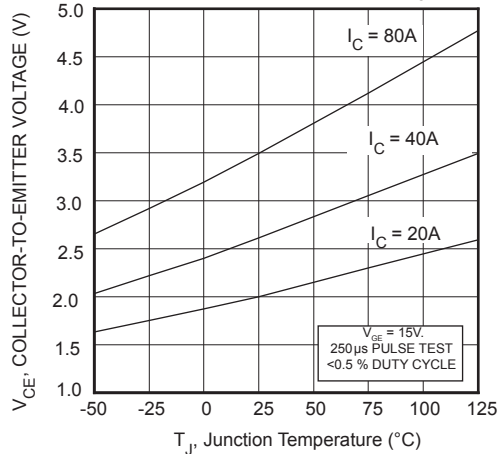


FIGURE 3, On State Voltage vs Junction Temperature

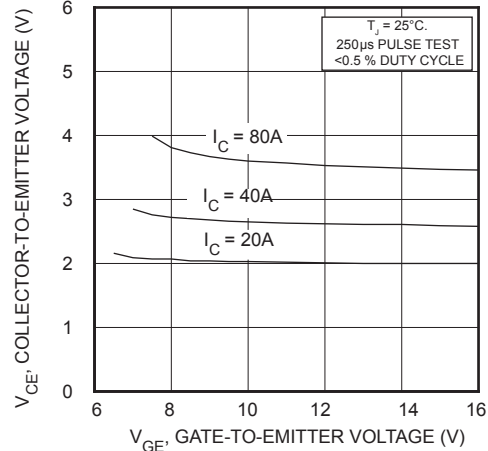


FIGURE 5, On State Voltage vs Gate-to-Emitter Voltage

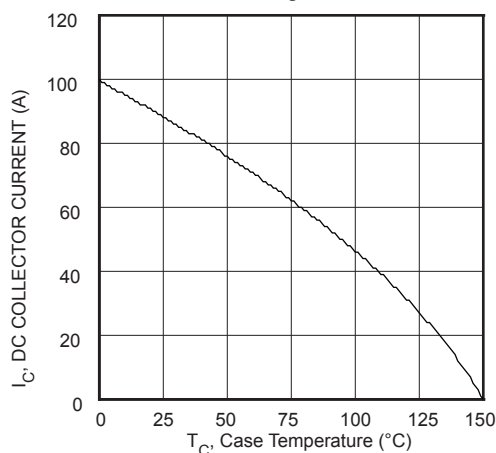


FIGURE 7, DC Collector Current vs Case Temperature

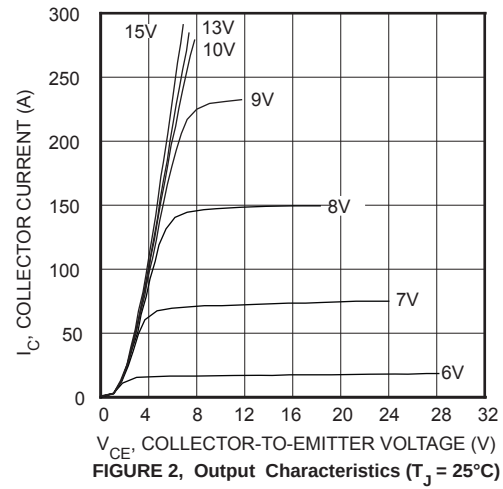


FIGURE 2, Output Characteristics ($T_J = 25^\circ\text{C}$)

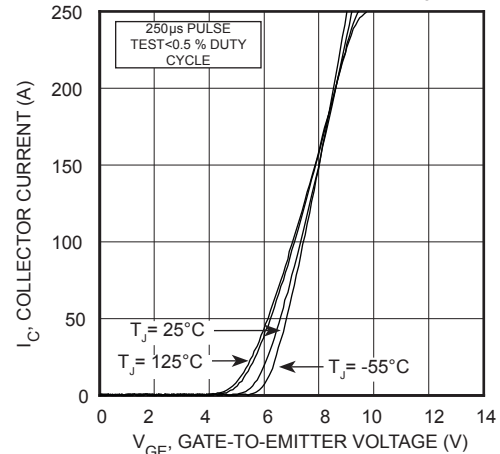


FIGURE 4, Transfer Characteristics

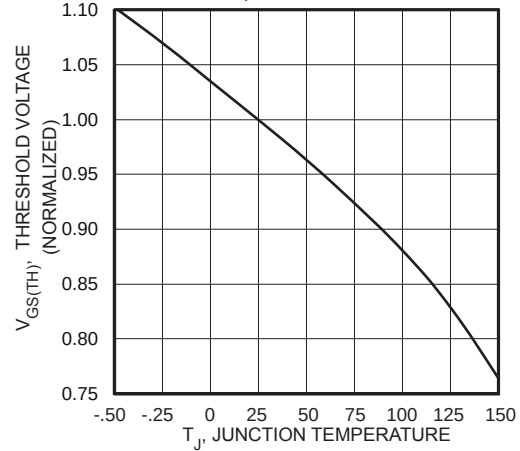


FIGURE 6, Threshold Voltage vs Junction Temperature

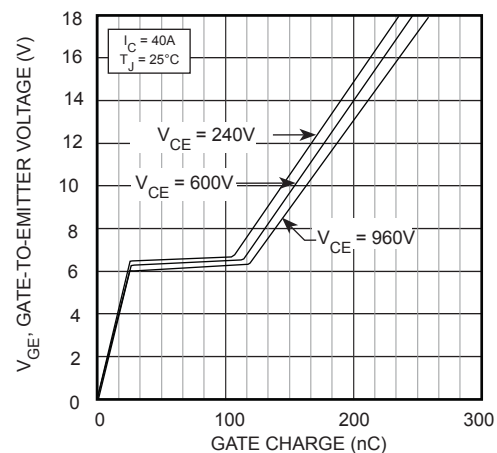


FIGURE 8, Gate charge

TYPICAL PERFORMANCE CURVES

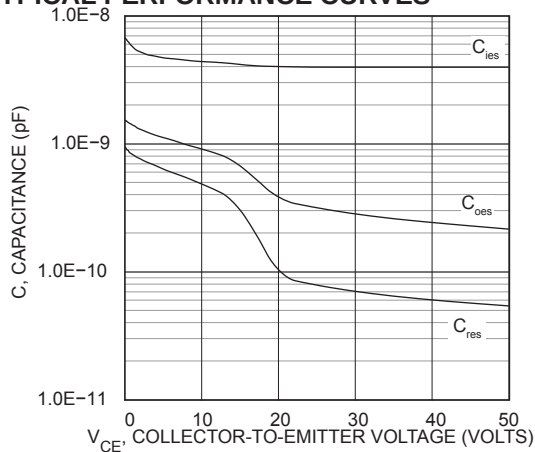


FIGURE 9, Capacitance vs Collector-To-Emitter Voltage

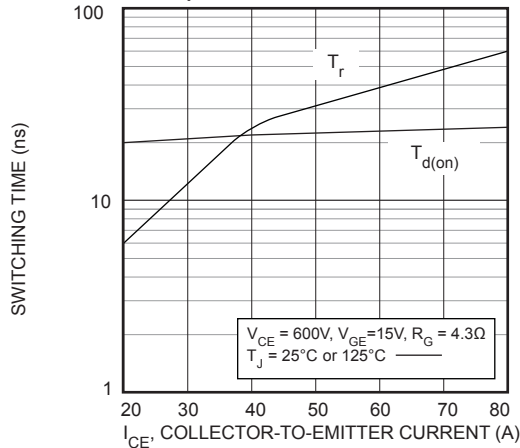


FIGURE 11, Turn-On Time vs Collector Current

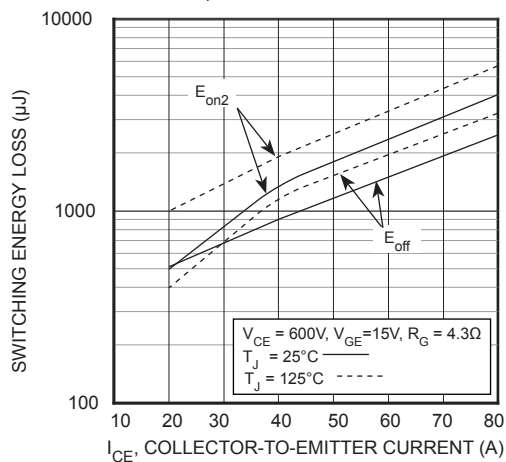


FIGURE 13, Energy Loss vs Collector Current

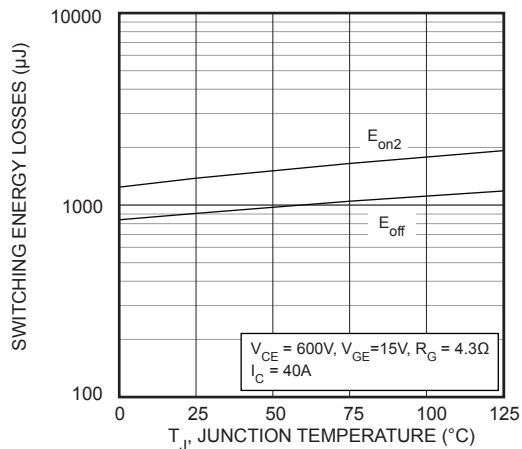


FIGURE 15, Energy Losses vs Junction Temperature

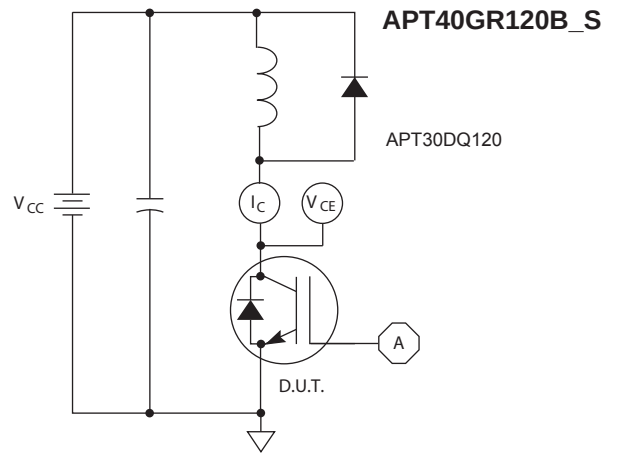


FIGURE 10, Inductive Switching Test Circuit

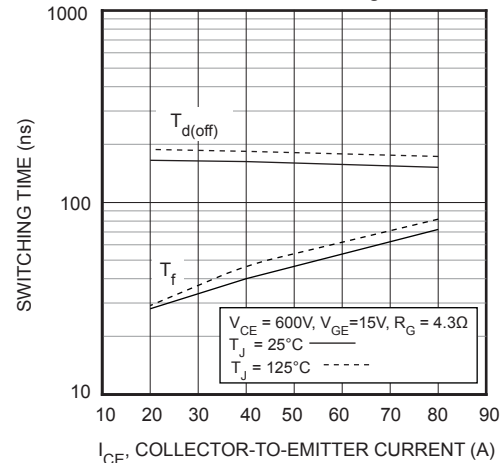


FIGURE 12, Turn-Off Time vs Collector Current

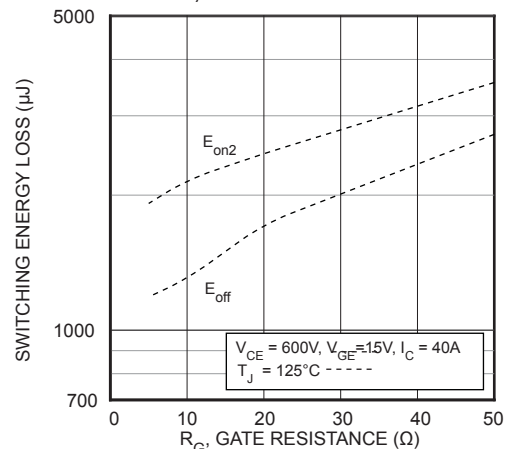


FIGURE 14, Energy Loss vs Gate Resistance

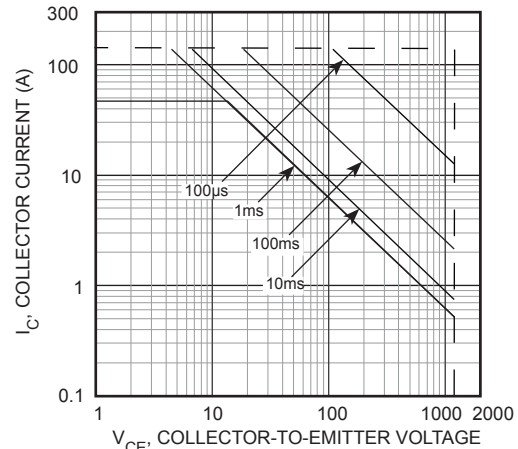


FIGURE 16, Minimum Switching Safe Operating Area

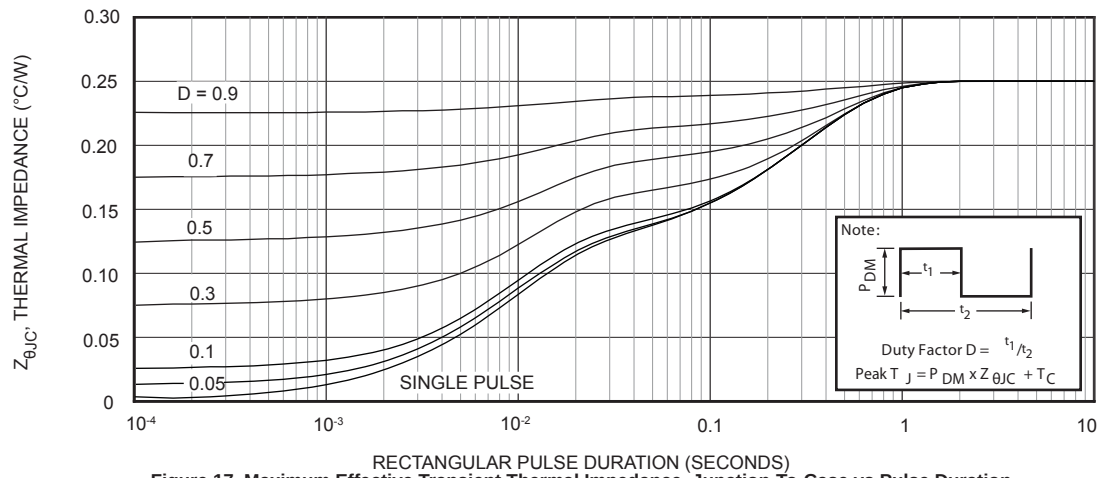
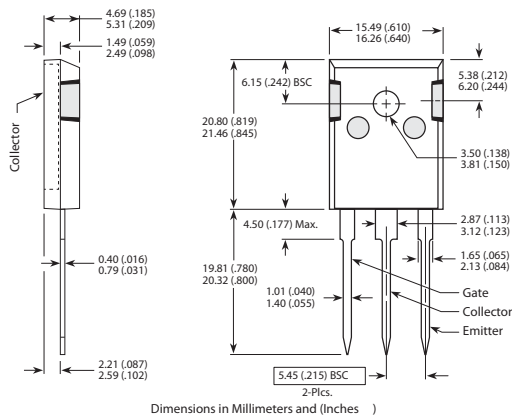


Figure 17, Maximum Effective Transient Thermal Impedance, Junction-To-Case vs Pulse Duration

TO-247 Package Outline

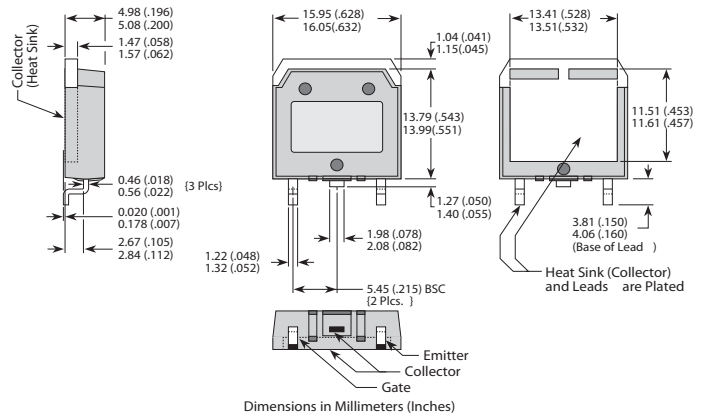
e3 SAC: 100% Sn Plating



Dimensions in Millimeters and (Inches)

D³PAK Package Outline

e3 SAC: 100% Sn Plating



Dimensions in Millimeters (Inches)